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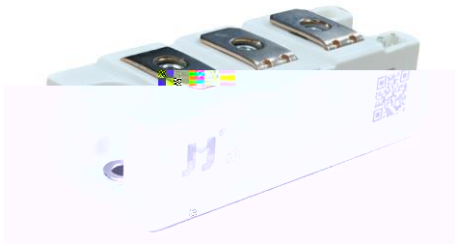

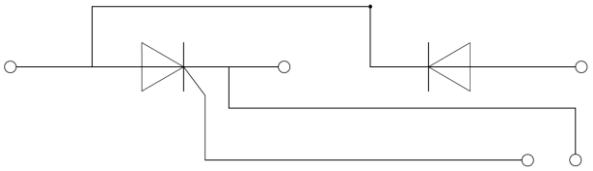

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FIG 1:Power dissipation vs. on-state current

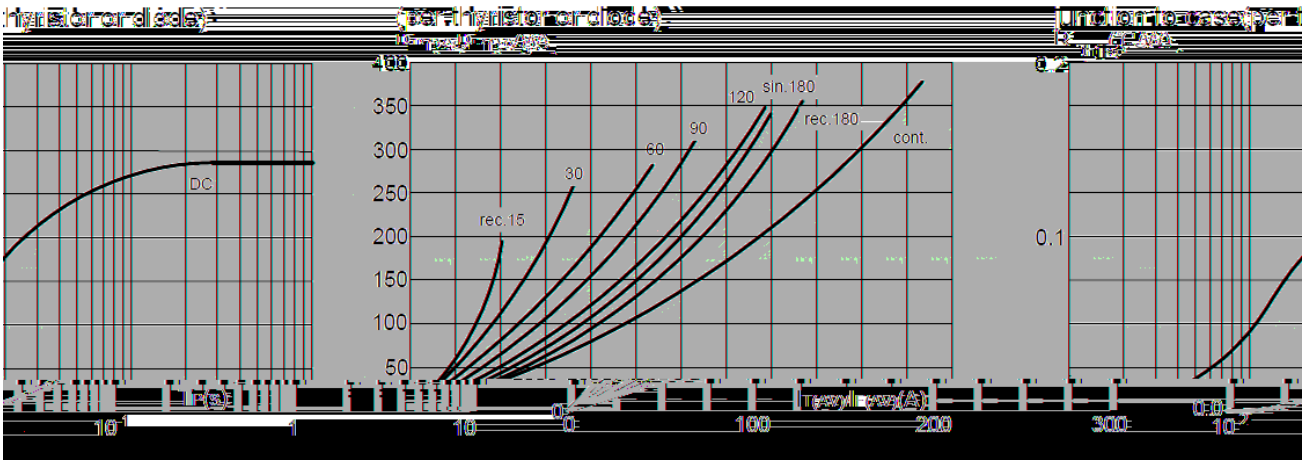


FIG 2: Maximum transient thermal impedance

FIG 3:Forward characteristics (per thyristor or diode)

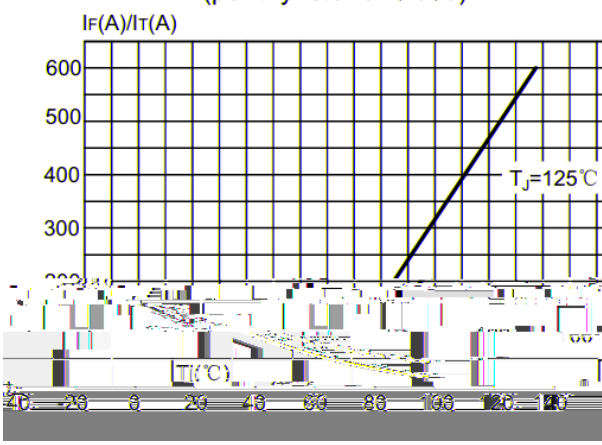


FIG 4: Relative variation of gate trigger current, holding current and latching current versus junction temperature

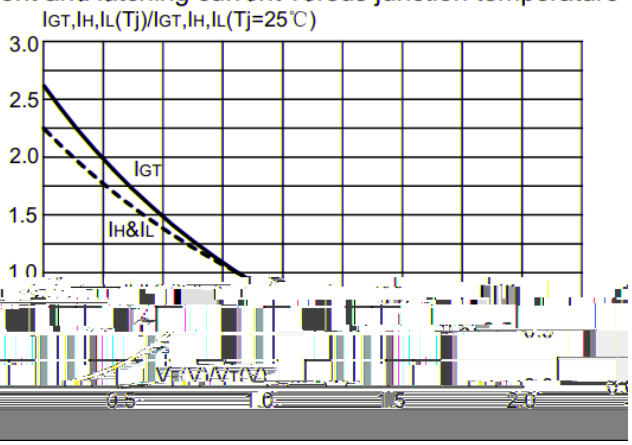


FIG 5 Gate trigger characteristics

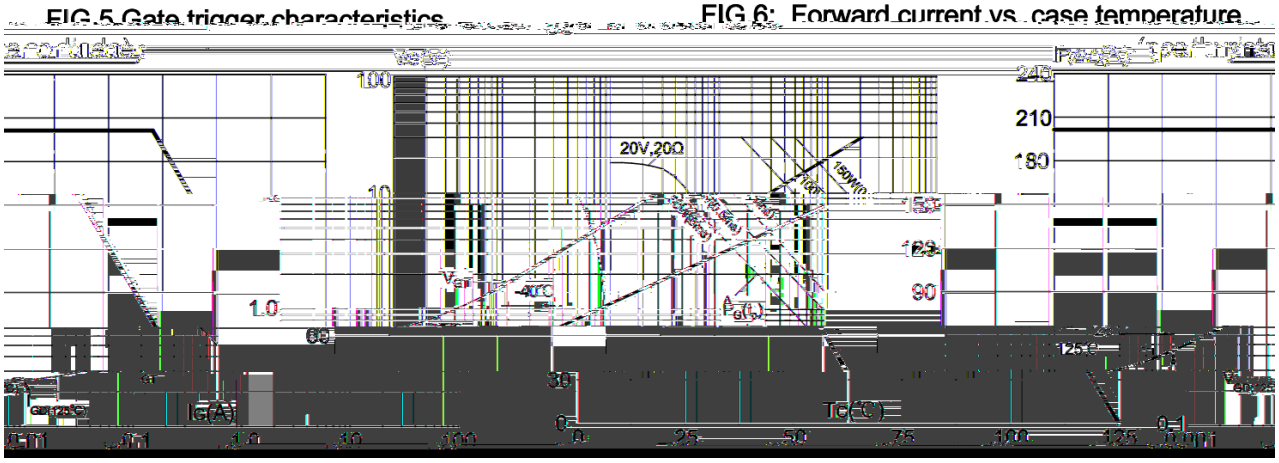


FIG 6: Forward current vs. case temperature